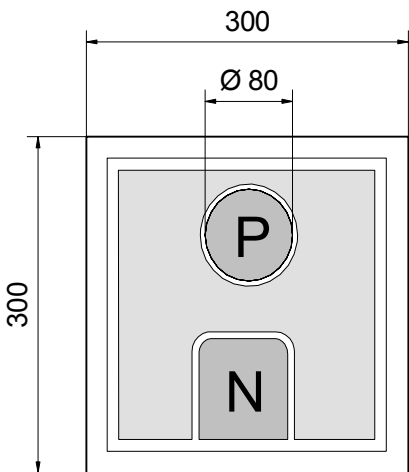


Radiation	Type	Technology	Electrodes
Blue	Standard	InGaN/Al <sub>2</sub> O <sub>3</sub>	Both on top side

	typ. dimensions in $\mu\text{m}$ ( $\pm 20 \mu\text{m}$ )
	<u>typ. thickness</u> 90 ( $\pm 20$ ) $\mu\text{m}$  <u>front side metalization</u> Au-alloy, 0.5 $\mu\text{m}$  <u>backside metalization</u> Al-alloy, 1.5 $\mu\text{m}$

### Maximum Ratings

$T_{\text{amb}} = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Test conditions	Symbol	Value	Unit
Forward current (DC)		$I_F$	30	mA
Peak forward current	( $t_p \leq 50 \mu\text{s}$ , $t_p/T = 1/2$ )	$I_{FM}$	100	mA
Operating temperature range		$T_{\text{amb}}$	-40 to +85	$^\circ\text{C}$
Storage temperature range		$T_{\text{stg}}$	-40 to +100	$^\circ\text{C}$

### Optical and Electrical Characteristics

$T_{\text{amb}} = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 20 \text{ mA}$	$V_F$		3.3	3.5	V
Reverse voltage	$I_F = 10 \mu\text{A}$	$V_R$	5			V
Luminous intensity <sup>1</sup>	$I_F = 20 \text{ mA}$	$I_v$	50	60		mcd
Peak wavelength	$I_F = 20 \text{ mA}$	$\lambda_p$	450	460	470	nm
Dominant wavelength	$I_F = 20 \text{ mA}$	$\lambda_D$		463		nm
Spectral bandwidth at 50%	$I_F = 20 \text{ mA}$	$\Delta\lambda_{0.5}$		25		nm
Switching time	$I_F = 20 \text{ mA}$	$t_r, t_f$		20		ns

<sup>1</sup>Measured on bare chip on TO-18 header with *EPIGAP* equipment

### Labeling

Type	Lot N°	$I_v(\text{typ})$ [mcd]	$V_F(\text{typ})$ [V]	Quantity
ELC-460-34				

**Packing:** Chips on adhesive film with wire-bond side on top